# NCV8133

# 500 mA, Very Low Dropout Bias Rail CMOS Voltage Regulator

The NCV8133 is a 500 mA VLDO equipped with NMOS pass transistor and a separate bias supply voltage ($V_{BIAS}$). The device provides very stable, accurate output voltage with low noise suitable for space constrained, noise sensitive applications. In order to optimize performance for battery operated portable applications, the NCV8133 features low $I_Q$ consumption. The XDFN6 1.2 mm x 1.2 mm package is optimized for use in space constrained applications.

### Features

- Input Voltage Range: 0.8 V to 5.5 V
- Bias Voltage Range: 2.4 V to 5.5 V
- Fixed Output Voltage Device
- Output Voltage Range: 0.8 V to 2.1 V
- ±1.5% Accuracy over Temperature, 0.5% $V_{OUT}$ @ 25°C
- Ultra−Low Dropout: Typ. 140 mV at 500 mA
- Very Low Bias Input Current of Typ. 80 μA
- Very Low Bias Input Current in Disable Mode: Typ. 0.5 μA
- Logic Level Enable Input for ON/OFF Control
- Output Active Discharge Option Available
- Stable with a 2.2 μF Ceramic Capacitor
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q100 Qualified and PPAP Capable; Device Temperature Grade 1: −40°C to +125°C Ambient Operating Temperature Range
- These are Pb−Free Devices

### Typical Applications

- Automotive, Consumer and Industrial Equipment Point of Load Regulation
- Battery−powered Equipment
- FPGA, DSP and Logic Power Supplies
- Switching Power Supply Post Regulation
- Cameras, DVRs, STB and Camcorders

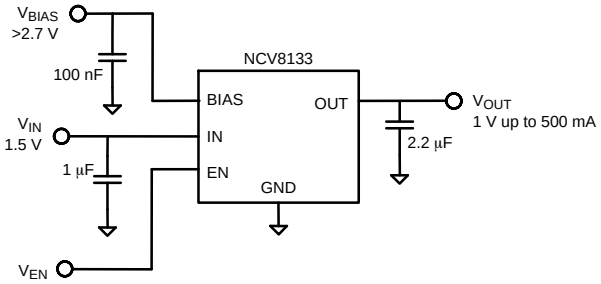



**Figure 1. Typical Application Schematics**

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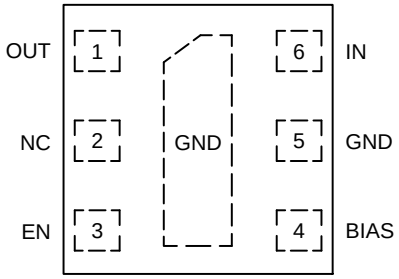
**XDFN6**
**CASE 711AT**

**MARKING DIAGRAM**




XX = Specific Device Code
M = Date Code

**PIN CONNECTIONS**

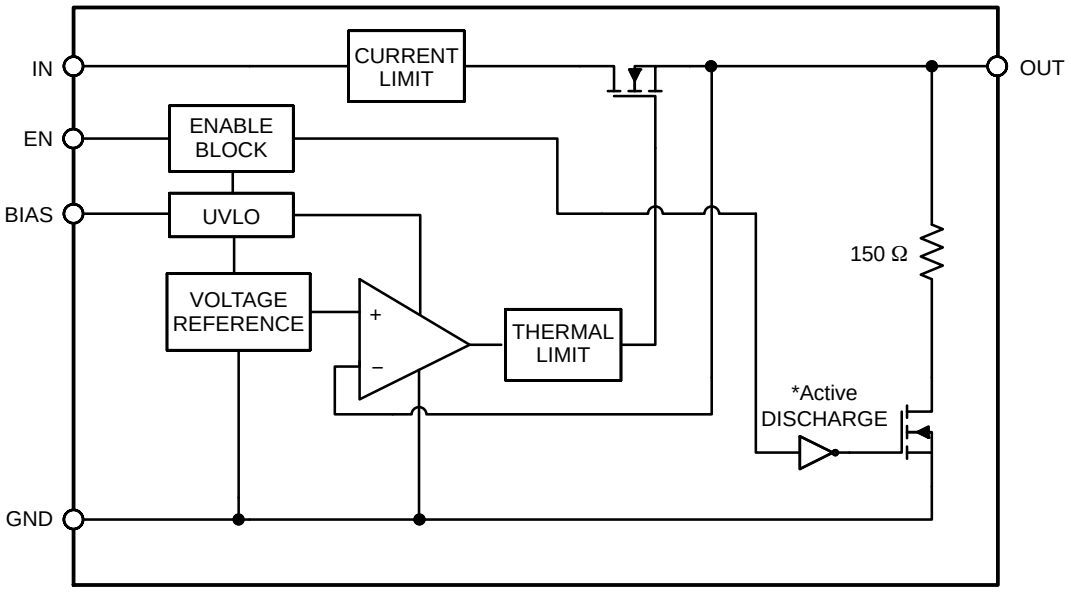



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**ORDERING INFORMATION**

See detailed ordering and shipping information on page 10 of this data sheet.

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*Active output discharge function is present only in NCV8133AMXyyyTCG devices.
yyy denotes the particular output voltage option.

**Figure 2. Simplified Schematic Block Diagram**

## PIN FUNCTION DESCRIPTION

| Pin No. XDFN6 | Pin Name | Description |
|---|---|---|
| 1 | OUT | Regulated Output Voltage pin |
| 2 | N/C | Not internally connected (Note 1) |
| 3 | EN | Enable pin. Driving this pin high enables the regulator. Driving this pin low puts the regulator into shutdown mode. |
| 4 | BIAS | Bias voltage supply for internal control circuits. This pin is monitored by internal Under-Voltage Lockout Circuit. |
| 5 | GND | Ground |
| 6 | IN | Input Voltage Supply pin |
| Pad | | Should be soldered to the ground plane for increased thermal performance. |

1. True no connect. Printed circuit board traces are allowable

## ABSOLUTE MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|---|---|---|
| Input Voltage (Note 2) | $V_{IN}$ | −0.3 to 6 | V |
| Output Voltage | $V_{OUT}$ | −0.3 to ($V_{IN}$+0.3) ≤ 6 | V |
| Chip Enable, Bias and Adj Input | $V_{EN}$, $V_{BIAS}$ | −0.3 to 6 | V |
| Output Short Circuit Duration | $t_{SC}$ | unlimited | s |
| Maximum Junction Temperature | $T_J$ | 150 | °C |
| Storage Temperature | $T_{STG}$ | −55 to 150 | °C |
| ESD Capability, Human Body Model (Note 3) | $ESD_{HBM}$ | 2000 | V |
| ESD Capability, Machine Model (Note 3) | $ESD_{MM}$ | 200 | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

2. Refer to ELECTRICAL CHARACTERISTICS and APPLICATION INFORMATION for Safe Operating Area.
3. This device series incorporates ESD protection (except OUT pin) and is tested by the following methods:
   ESD Human Body Model tested per AEC−Q100−002
   ESD Machine Model tested per AEC−Q100−003
   Latchup Current Maximum Rating ≤ 150 mA per AEC−Q100−004.

## RECOMMENDED OPERATING CONDITIONS

| Rating | Symbol | Min | Max | Unit |
|---|---|---|---|---|
| Input Voltage | $V_{IN}$ | ($V_{OUT}$ + $V_{DO_IN}$) | 5.5 | V |
| Bias Voltage | $V_{BIAS}$ | ($V_{OUT}$ + 1.4) ≥ 2.4 | 5.5 | V |
| Junction Temperature | $T_J$ | −40 | +125 | °C |

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## THERMAL CHARACTERISTICS

| Rating | Symbol | Value | Unit |
|---|---|---|---|
| Thermal Characteristics, XDFN6 1.2 mm x 1.2 mm Thermal Resistance, Junction−to−Air | $R_{\theta JA}$ | 170 | °C/W |

**ELECTRICAL CHARACTERISTICS** $-40°C \le T_J \le 125°C$; $V_{BIAS}$ = 2.7 V or ($V_{OUT}$ + 1.6 V), whichever is greater, $V_{IN} = V_{OUT(NOM)}$ + 0.3 V, $I_{OUT}$ = 1 mA, $V_{EN}$ = 1 V, unless otherwise noted. $C_{IN}$ = 1 μF, $C_{OUT}$ = 2.2 μF. Typical values are at $T_J$ = +25°C. Min/Max values are for $-40°C \le T_J \le 125°C$ unless otherwise noted. (Note 4)

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Operating Input Voltage Range | | $V_{IN}$ | $V_{OUT}$ + $V_{DO}$ | | 5.5 | V |
| Operating Bias Voltage Range | | $V_{BIAS}$ | ($V_{OUT}$ + 1.40) ≥ 2.4 | | 5.5 | V |
| Undervoltage Lock−out | $V_{BIAS}$ Rising<br>Hysteresis | UVLO | | 1.6<br>0.2 | | V |
| Output Voltage Accuracy | | $V_{OUT}$ | | ±0.5 | | % |
| Output Voltage Accuracy | $-40°C \le T_J \le 125°C$, $V_{OUT(NOM)}$ + 0.3 V ≤ $V_{IN}$ ≤ $V_{OUT(NOM)}$ + 1.0 V, 2.7 V or ($V_{OUT(NOM)}$ + 1.6 V), whichever is greater < $V_{BIAS}$ < 5.5 V, 1 mA < $I_{OUT}$ < 500 mA | $V_{OUT}$ | −1.5 | | +1.5 | % |
| $V_{IN}$ Line Regulation | $V_{OUT(NOM)}$ + 0.3 V ≤ $V_{IN}$ ≤ 5.0 V | $Line_{Reg}$ | | 0.01 | | %/V |
| $V_{BIAS}$ Line Regulation | 2.7 V or ($V_{OUT(NOM)}$ + 1.6 V), whichever is greater < $V_{BIAS}$ < 5.5 V | $Line_{Reg}$ | | 0.01 | | %/V |
| Load Regulation | $I_{OUT}$ = 1 mA to 500 mA | $Load_{Reg}$ | | 1.5 | | mV |
| $V_{IN}$ Dropout Voltage | $I_{OUT}$ = 150 mA (Note 5) | $V_{DO}$ | | 37 | 90 | mV |
| | $I_{OUT}$ = 500 mA (Note 5) | $V_{DO}$ | | 140 | 300 | |
| $V_{BIAS}$ Dropout Voltage | $I_{OUT}$ = 500 mA, $V_{IN} = V_{BIAS}$ (Notes 5, 6) | $V_{DO}$ | | 1.1 | 1.5 | V |
| Output Current Limit | $V_{OUT}$ = 90% $V_{OUT(NOM)}$ | $I_{CL}$ | 550 | 800 | 1100 | mA |
| Bias Pin Operating Current | $V_{BIAS}$ = 2.7 V | $I_{BIAS}$ | | 80 | 110 | μA |
| Bias Pin Disable Current | $V_{EN}$ ≤ 0.4 V | $I_{BIAS(DIS)}$ | | 0.5 | 1.5 | μA |
| Vinput Pin Disable Current | $V_{EN}$ ≤ 0.4 V | $I_{VIN(DIS)}$ | | 0.5 | 1.5 | μA |
| EN Pin Threshold Voltage | EN Input Voltage “H” | $V_{EN(H)}$ | 0.9 | | | V |
| | EN Input Voltage “L” | $V_{EN(L)}$ | | | 0.4 | |
| EN Pull Down Current | $V_{EN}$ = 5.5 V | $I_{EN}$ | | 0.3 | 1.5 | μA |
| Turn−On Time | From assertion of $V_{EN}$ to $V_{OUT}$ = 98% $V_{OUT(NOM)}$. $V_{OUT(NOM)}$ = 1.0 V | $t_{ON}$ | | 150 | | μs |
| Power Supply Rejection Ratio | $V_{IN}$ to $V_{OUT}$, f = 1 kHz, $I_{OUT}$ = 150 mA, $V_{IN} \ge V_{OUT}$ +0.5 V | PSRR($V_{IN}$) | | 70 | | dB |
| | $V_{BIAS}$ to $V_{OUT}$, f = 1 kHz, $I_{OUT}$ = 150 mA, $V_{IN} \ge V_{OUT}$ +0.5 V | PSRR($V_{BIAS}$) | | 80 | | dB |
| Output Noise Voltage | $V_{IN} = V_{OUT}$ +0.5 V, $V_{OUT(NOM)}$ = 1.0 V, f = 10 Hz to 100 kHz | $V_N$ | | 40 | | $\mu V_{RMS}$ |
| Thermal Shutdown Threshold | Temperature increasing | | | 160 | | °C |
| | Temperature decreasing | | | 140 | | |
| Output Discharge Pull−Down | $V_{EN}$ ≤ 0.4 V, $V_{OUT}$ = 0.5 V, NCV8133A options only | $R_{DISCH}$ | | 150 | | Ω |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Performance guaranteed over the indicated operating temperature range by design and/or characterization. Production tested at $T_A$ = 25°C. Low duty cycle pulse techniques are used during the testing to maintain the junction temperature as close to ambient as possible.
5. Dropout voltage is characterized when $V_{OUT}$ falls 3% below $V_{OUT(NOM)}$.
6. For output voltages below 0.9 V, $V_{BIAS}$ dropout voltage does not apply due to a minimum Bias operating voltage of 2.4 V.

## TYPICAL CHARACTERISTICS

At $T_J$ = +25°C, $V_{IN}$ = $V_{OUT(TYP)}$ + 0.3 V, $V_{BIAS}$ = 2.7 V, $V_{EN}$ = $V_{BIAS}$, $V_{OUT(NOM)}$ = 1.0 V, $I_{OUT}$ = 500 mA, $C_{IN}$ = 1 μF, $C_{BIAS}$ = 0.1 μF, and $C_{OUT}$ = 2.2 μF (effective capacitance), unless otherwise noted.

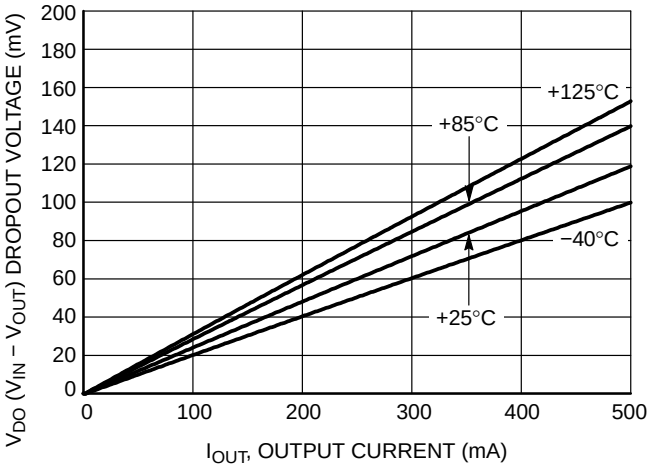



**Figure 3. $V_{IN}$ Dropout Voltage vs. $I_{OUT}$ and Temperature $T_J$**

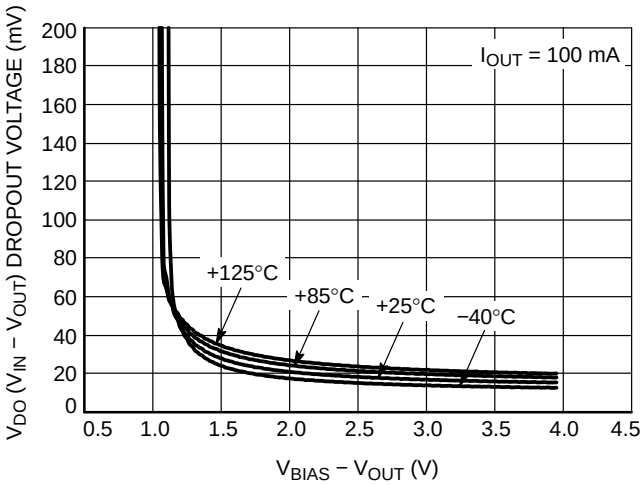



**Figure 4. $V_{IN}$ Dropout Voltage vs. ($V_{BIAS}$ − $V_{OUT}$) and Temperature $T_J$**

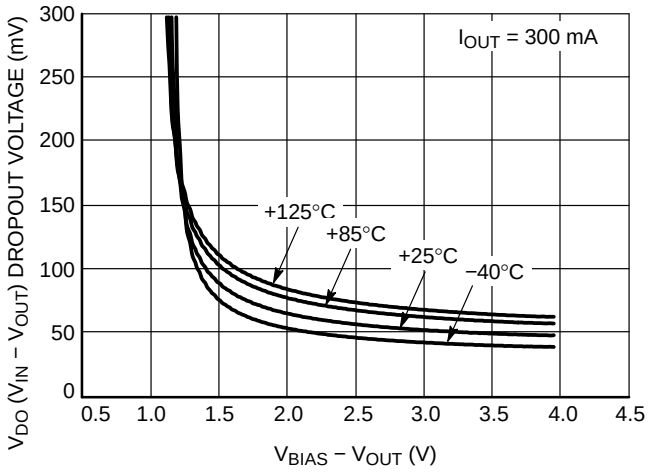



**Figure 5. $V_{IN}$ Dropout Voltage vs. ($V_{BIAS}$ − $V_{OUT}$) and Temperature $T_J$**

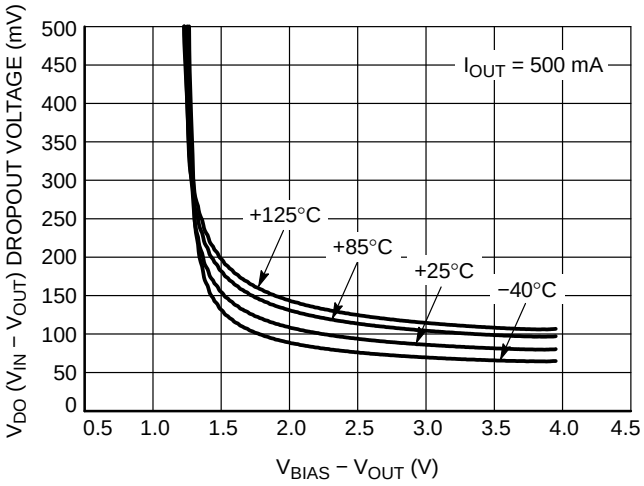



**Figure 6. $V_{IN}$ Dropout Voltage vs. ($V_{BIAS}$ − $V_{OUT}$) and Temperature $T_J$**

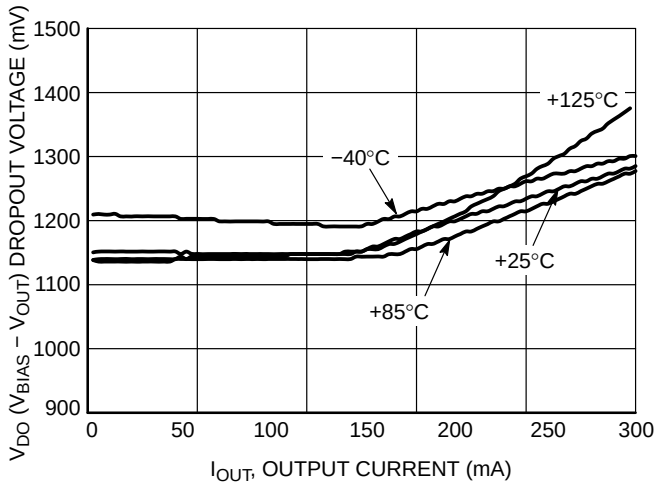



**Figure 7. $V_{BIAS}$ Dropout Voltage vs. $I_{OUT}$ and Temperature $T_J$**

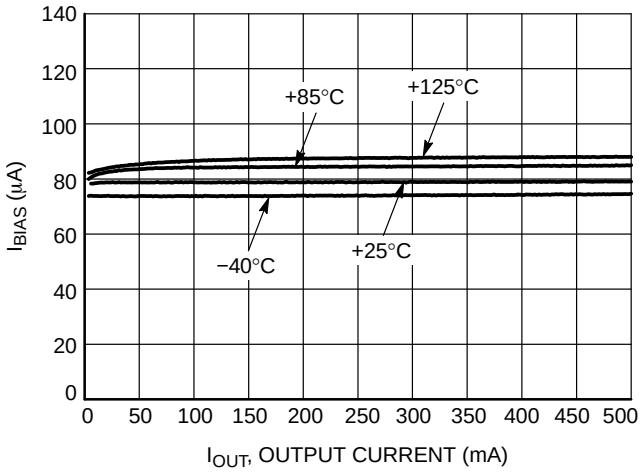



**Figure 8. BIAS Pin Current vs. $I_{OUT}$ and Temperature $T_J$**

## TYPICAL CHARACTERISTICS

At $T_J$ = +25°C, $V_{IN}$ = $V_{OUT(TYP)}$ + 0.3 V, $V_{BIAS}$ = 2.7 V, $V_{EN}$ = $V_{BIAS}$, $V_{OUT(NOM)}$ = 1.0 V, $I_{OUT}$ = 500 mA, $C_{IN}$ = 1 μF, $C_{BIAS}$ = 0.1 μF, and $C_{OUT}$ = 2.2 μF (effective capacitance), unless otherwise noted.

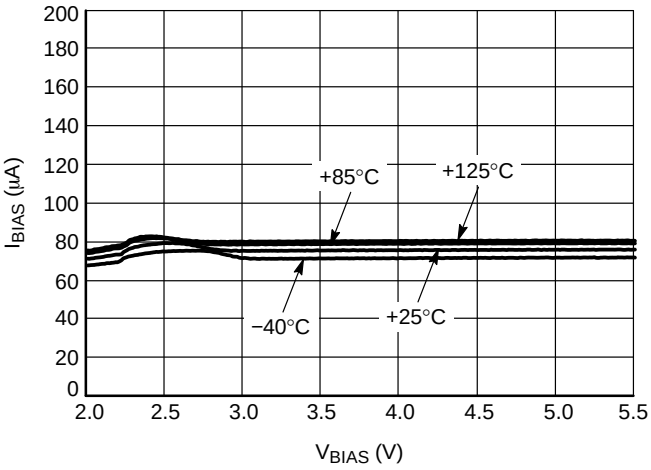



**Figure 9. BIAS Pin Current vs. $V_{BIAS}$ and Temperature $T_J$**

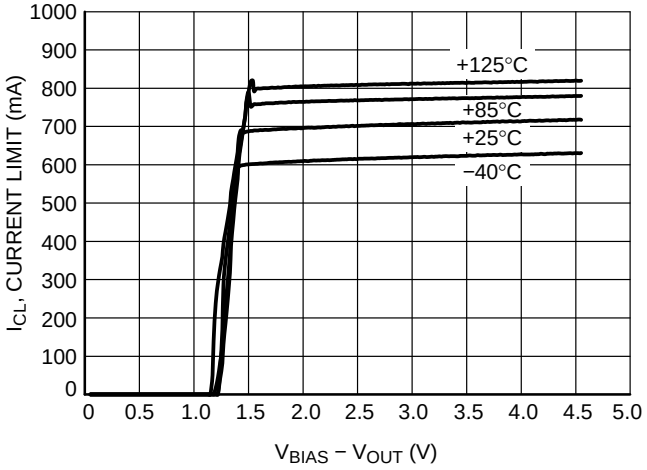



**Figure 10. Current Limit vs. ($V_{BIAS}$ − $V_{OUT}$)**

## TYPICAL CHARACTERISTICS

At $T_J$ = +25°C, $V_{IN}$ = $V_{OUT(TYP)}$ + 0.3 V, $V_{BIAS}$ = 2.7 V, $V_{EN}$ = $V_{BIAS}$, $V_{OUT(NOM)}$ = 1.0 V, $I_{OUT}$ = 500 mA, $C_{IN}$ = 1 μF, $C_{BIAS}$ = 0.1 μF, and $C_{OUT}$ = 2.2 μF (effective capacitance), unless otherwise noted.

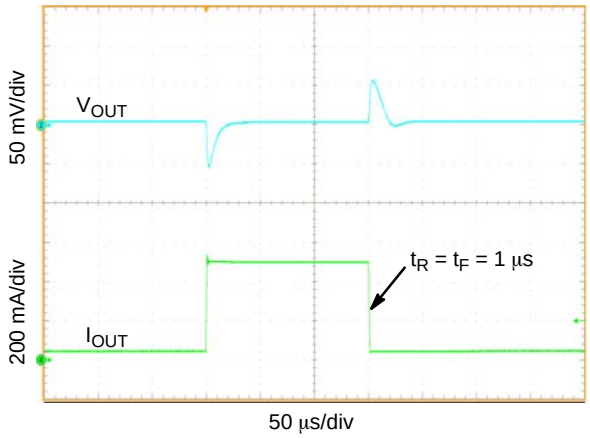



**Figure 11. Load Transient Response, $I_{OUT}$ = 50 mA to 500 mA, $C_{OUT}$ = 10 μF**

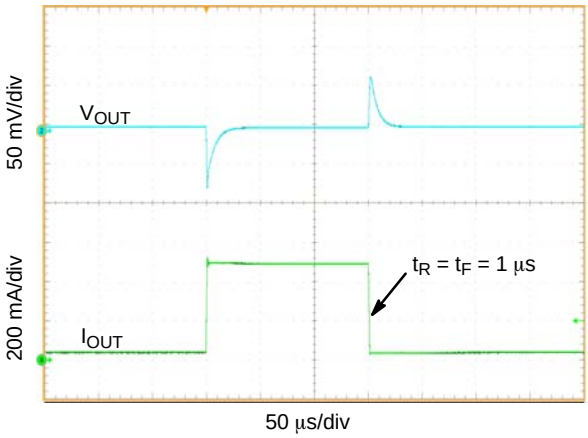



**Figure 12. Load Transient Response, $I_{OUT}$ = 50 mA to 500 mA, $C_{OUT}$ = 2.2 μF**

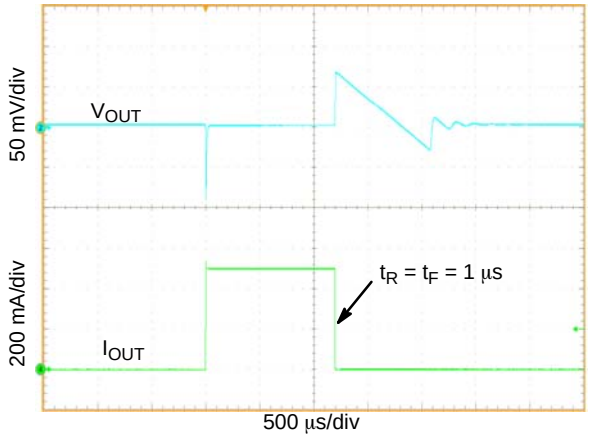



**Figure 13. Load Transient Response, $I_{OUT}$ = 1 mA to 500 mA, $C_{OUT}$ = 10 μF**

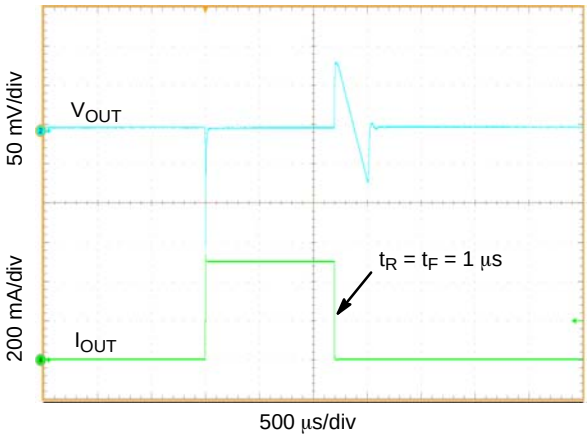



**Figure 14. Load Transient Response, $I_{OUT}$ = 1 mA to 500 mA, $C_{OUT}$ = 2.2 μF**

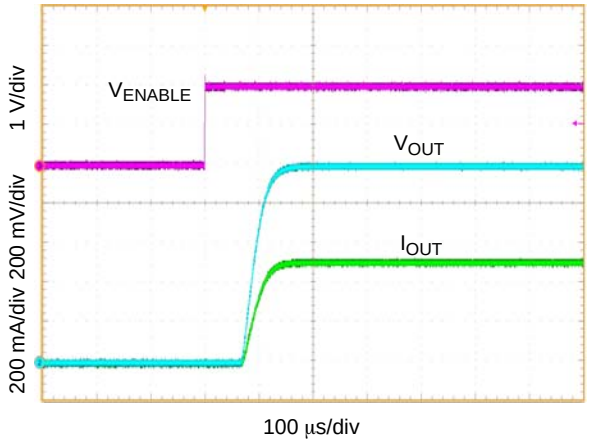



**Figure 15. Enable Turn−on Response, Output Resistive Load 500 mA, $C_{OUT}$ = 10 μF**

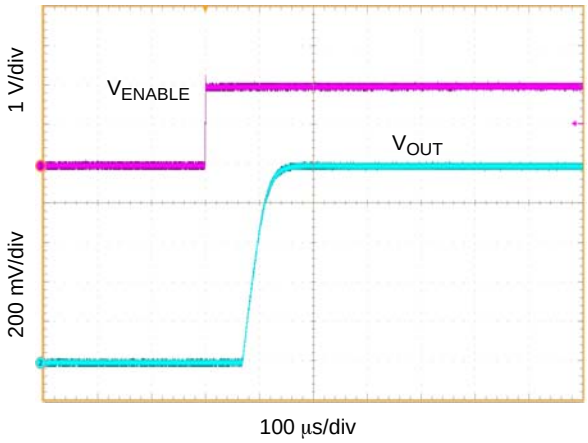



**Figure 16. Enable Turn−on Response, $I_{OUT}$ = 0 mA, $C_{OUT}$ = 2.2 μF**

## TYPICAL CHARACTERISTICS

At $T_J$ = +25°C, $V_{IN}$ = $V_{OUT(TYP)}$ + 0.3 V, $V_{BIAS}$ = 2.7 V, $V_{EN}$ = $V_{BIAS}$, $V_{OUT(NOM)}$ = 1.0 V, $I_{OUT}$ = 500 mA, $C_{IN}$ = 1 μF, $C_{BIAS}$ = 0.1 μF, and $C_{OUT}$ = 2.2 μF (effective capacitance), unless otherwise noted.

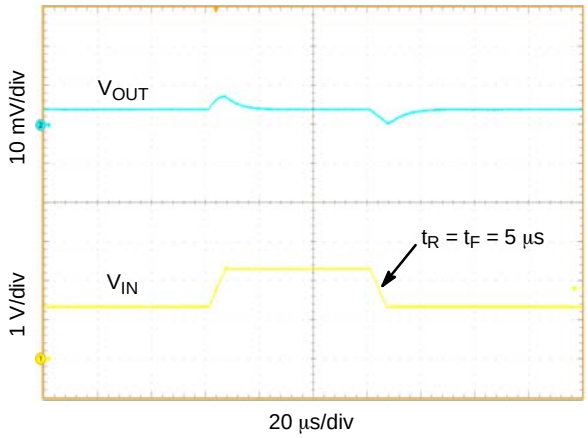



**Figure 17. $V_{IN}$ Line Transient Response, $V_{IN}$ = 1.3 V to 2.3 V, $I_{OUT}$ = 100 mA, $C_{OUT}$ = 10 μF**

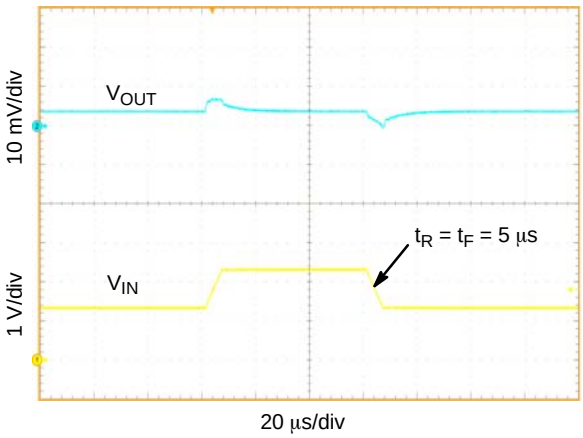



**Figure 18. $V_{IN}$ Line Transient Response, $V_{IN}$ = 1.3 V to 2.3 V, $I_{OUT}$ = 100 mA, $C_{OUT}$ = 2.2 μF**

## APPLICATIONS INFORMATION

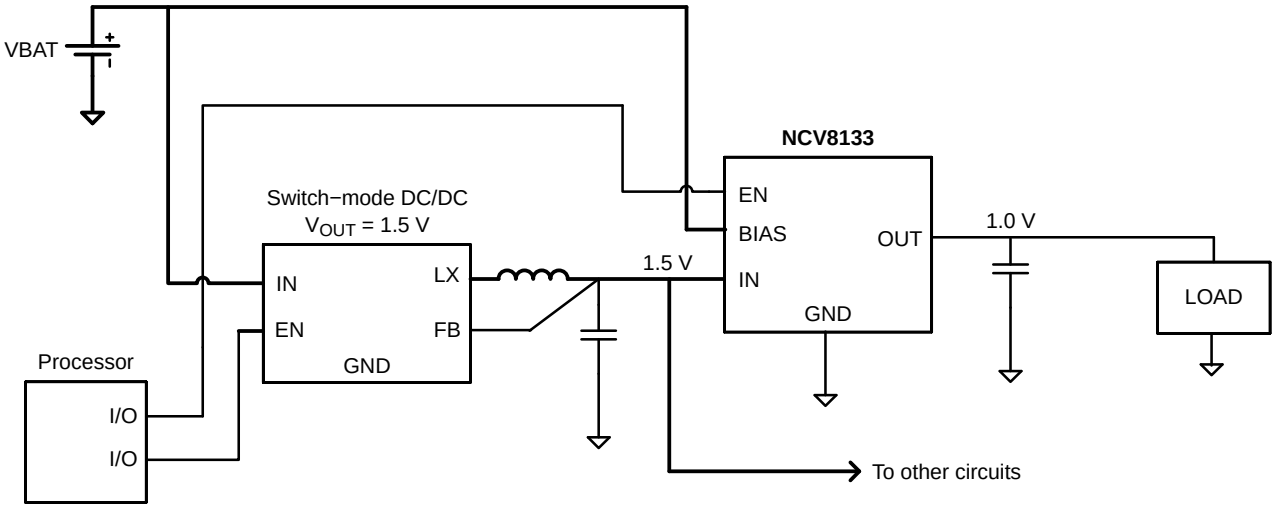



**Figure 19. Typical Application: Low−Voltage DC/DC Post−Regulator with ON/OFF Functionality**

The NCV8133 dual−rail very low dropout voltage regulator is using NMOS pass transistor for output voltage regulation from $V_{IN}$ voltage. All the low current internal control circuitry is powered from the $V_{BIAS}$ voltage.

The use of an NMOS pass transistor offers several advantages in applications. Unlike PMOS topology devices, the output capacitor has reduced impact on loop stability. Vin to Vout operating voltage difference can be very low compared with standard PMOS regulators in very low Vin applications.

The NCV8133 offers smooth monotonic start-up. The controlled voltage rising limits the inrush current.

The Enable (EN) input is equipped with internal hysteresis.

NCV8133 is a Fixed Voltage linear regulator.

### Dropout Voltage

Because of two power supply inputs $V_{IN}$ and $V_{BIAS}$ and one $V_{OUT}$ regulator output, there are two Dropout voltages specified.

The first, the $V_{IN}$ Dropout voltage is the voltage difference ($V_{IN} - V_{OUT}$) when $V_{OUT}$ starts to decrease by percent specified in the Electrical Characteristics table. $V_{BIAS}$ is high enough; specific value is published in the Electrical Characteristics table.

The second, $V_{BIAS}$ dropout voltage is the voltage difference ($V_{BIAS} - V_{OUT}$) when $V_{IN}$ and $V_{BIAS}$ pins are joined together and $V_{OUT}$ starts to decrease.

### Input and Output Capacitors

The device is designed to be stable for ceramic output capacitors with Effective capacitance in the range from 2.2 μF to 10 μF. The device is also stable with multiple capacitors in parallel, having the total effective capacitance in the specified range.

In applications where no low input supplies impedance available (PCB inductance in $V_{IN}$ and/or $V_{BIAS}$ inputs as example), the recommended $C_{IN}$ = 1 μF and $C_{BIAS}$ = 0.1 μF or greater. Ceramic capacitors are recommended**.** For the best performance all the capacitors should be connected to the NCV8133 respective pins directly in the device PCB copper layer, not through vias having not negligible impedance.

When using small ceramic capacitor, their capacitance is not constant but varies with applied DC biasing voltage, temperature and tolerance. The effective capacitance can be much lower than their nominal capacitance value, most importantly in negative temperatures and higher LDO output voltages. That is why the recommended Output capacitor capacitance value is specified as Effective value in the specific application conditions.

### Enable Operation

The enable pin will turn the regulator on or off. The threshold limits are covered in the electrical characteristics table in this data sheet. If the enable function is not to be used then the pin should be connected to $V_{IN}$ or $V_{BIAS}$.

### Current Limitation

The internal Current Limitation circuitry allows the device to supply the full nominal current and surges but protects the device against Current Overload or Short.

### Thermal Protection

Internal thermal shutdown (TSD) circuitry is provided to protect the integrated circuit in the event that the maximum junction temperature is exceeded. When TSD activated , the regulator output turns off. When cooling down under the low temperature threshold, device output is activated again. This TSD feature is provided to prevent failures from accidental overheating.

### Power Dissipation

The maximum power dissipation supported by the device is dependent upon board design and layout. Mounting pad configuration on the PCB, the board material, and the ambient temperature affect the rate of junction temperature rise for the part. For reliable operation, junction temperature should be limited to +125°C.

## ORDERING INFORMATION

| Device | Nominal Output Voltage | Marking | Option | Package | Shipping† |
|---|---|---|---|---|---|
| NCV8133BMX080TCG | 0.80 V | JL | Non−Active Discharge | XDFN6 (Pb−Free) | 3000 / Tape & Reel |
| NCV8133BMX100TCG | 1.00 V | JM | | | |
| NCV8133BMX110TCG | 1.10 V | JD | | | |
| NCV8133BMX120TCG | 1.20 V | JE | | | |
| NCV8133BMX130TCG | 1.30 V | JN | | | |
| NCV8133BMX150TCG | 1.50 V | JF | | | |
| NCV8133BMX180TCG | 1.80 V | JG | | | |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

To order other package and voltage variants, please contact your ON Semiconductor sales representative

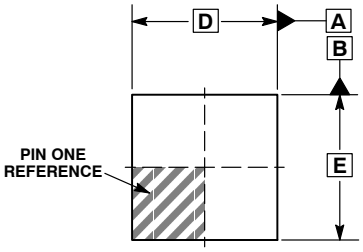
# MECHANICAL CASE OUTLINE
## PACKAGE DIMENSIONS

ON Semiconductor®

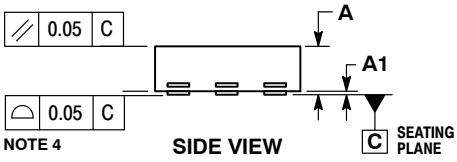
**XDFN6 1.20x1.20, 0.40P**
CASE 711AT
ISSUE C

**SCALE 4:1**

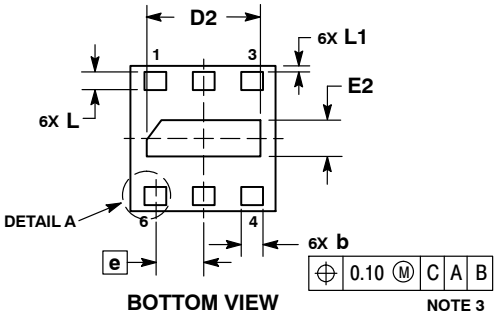
DATE 04 DEC 2015



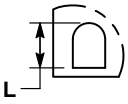

**TOP VIEW**




**SIDE VIEW**




**BOTTOM VIEW**




**DETAIL A**
**OPTIONAL CONSTRUCTION**

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO THE PLATED TERMINALS.
4. COPLANARITY APPLIES TO THE PAD AS WELL AS THE TERMINALS.

| | MILLIMETERS | | |
|---|---|---|---|
| DIM | MIN | TYP | MAX |
| A | 0.30 | 0.37 | 0.45 |
| A1 | 0.00 | 0.03 | 0.05 |
| b | 0.13 | 0.18 | 0.23 |
| D | 1.15 | 1.20 | 1.25 |
| D2 | 0.84 | 0.94 | 1.04 |
| E | 1.15 | 1.20 | 1.25 |
| E2 | 0.20 | 0.30 | 0.40 |
| e | 0.40 BSC | | |
| L | 0.15 | 0.20 | 0.25 |
| L1 | 0.00 | 0.05 | 0.10 |

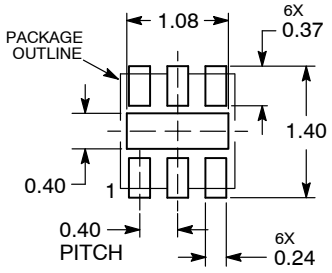
### GENERIC MARKING DIAGRAM*




XX = Specific Device Code
M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

### RECOMMENDED MOUNTING FOOTPRINT*




DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| | | |
|---|---|---|
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